

Abstracts

Transient Capless Annealing of Ion-Implanted PBN LEC GaAs for Monolithic Microwave Integrated Circuits

R.C. Clarke, G.W. Eldridge, S.K. Wang and W.F. Valek. "Transient Capless Annealing of Ion-Implanted PBN LEC GaAs for Monolithic Microwave Integrated Circuits." 1983 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 83.1 (1983 [MCS]): 31-35.

A method for high-temperature, capless activation of implanted gallium arsenide has been devised based on the recent availability of high-purity semi-insulating PBN LEC gallium arsenide both as implant host and stabilizing medium.

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